





**60V P-CHANNEL ENHANCEMENT MODE MOSFET** 

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub> T <sub>A</sub> = 25°C
-60V	125mΩ @ $V_{GS}$ = -10V	-3.4A
	190mΩ @ $V_{GS}$ = -4.5V	-2.8A

# **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor control
- Backlighting
- **DC-DC Converters**
- Power management functions

## **Features and Benefits**

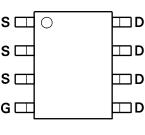
- Fast switching speed .
- Low input capacitance
- "Green" component and RoHS compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SO-8 •
- Case Material: Molded Plastic, "Green" Molding Compound. • UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See diagram below .
- Terminals: Finish Matte Tin annealed over Copper lead frame. • Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (approximate)

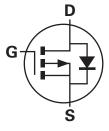


Top View





Top View



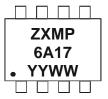
Equivalent Circuit

#### Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel	
ZXMP6A17N8TC	See below	13	12	2,500	

Notes: 1. Diodes, Inc. defines "Green" products as those which are RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

## Marking Information



ZXMP = Product Type Marking Code, Line 1 6A17 = Product Type Marking Code, Line 2 YYWW = Date Code Marking YY = Year (ex: 09 = 2009) WW = Week (01 - 53)



#### Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit	
Drain-Source voltage			V <sub>DSS</sub>	-60	V	
Gate-Source voltage			V <sub>GS</sub>	±20	V	
		(Note 3)		-3.42		
Continuous Drain current	$V_{GS} = 10V$	$T_{A} = 70^{\circ}C$ (Note 3)	ID	-2.73	A	
		(Note 2)		-2.7		
Pulsed Drain current	$V_{GS} = 10V$	(Note 4)	I <sub>DM</sub>	-15.6	A	
Continuous Source current (Body diode) (Note 3)		(Note 3)	Is	-3.4	A	
Pulsed Source current (Body diode) (Note 4)		(Note 4)	I <sub>SM</sub>	-15.6	А	

#### Thermal Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
Power dissipation Linear derating factor	(Note 2)	ſ	1.56 12.5	W	
	(Note 3)		2.5 20	mW/°C	
Thermal Desistance Junction to Ambient	(Note 2)	5	80		
Thermal Resistance, Junction to Ambient	(Note 3)	R <sub>θJA</sub>	50	°C/W	
Thermal Resistance, Junction to Lead	(Note 5)	R <sub>θJL</sub>	32		
Operating and storage temperature range		T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	۵°	

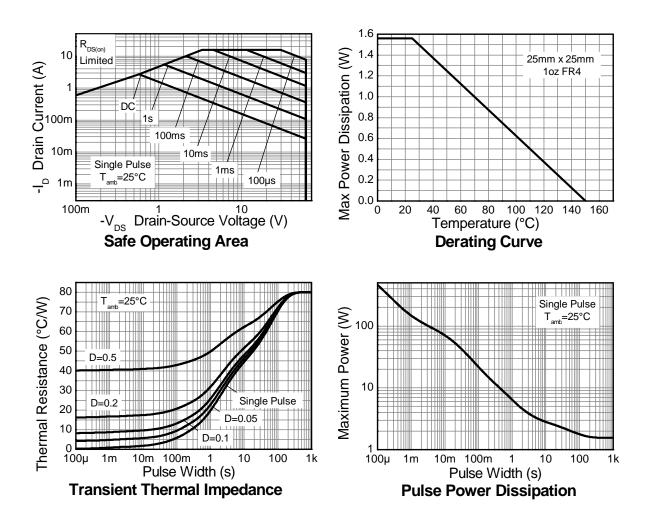
2. For a device surface mounted on 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is Notes: measured when operating in a steady-state condition.

3. Same as note (2), except the device is measured at t  $\leq$  10 sec.

4. Same as note (2), except the device is pulsed with D= 0.02 and pulse width  $300 \ \mu$ s. The pulse current is limited by the maximum junction temperature. 5. Thermal resistance from junction to solder-point (at the end of the drain lead).



# **Thermal Characteristics**





# Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

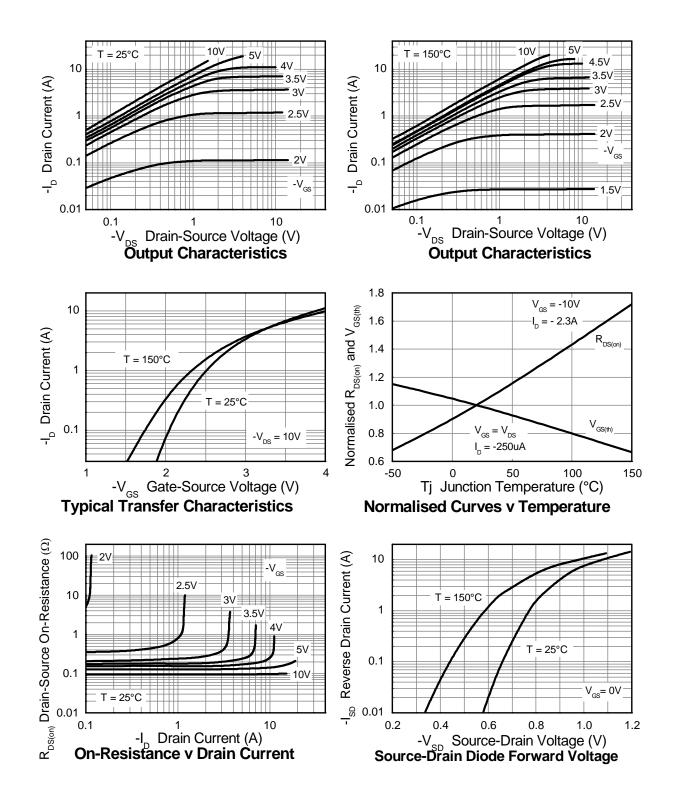
Characteristic	Symbol	Min	Тур	Max	Unit	Test	Condition
OFF CHARACTERISTICS						•	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	_	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-0.5	μΑ	$V_{DS} = -60V, V_{O}$	<sub>65</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V$	<sub>DS</sub> = 0V
ON CHARACTERISTICS							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0	_	_	V	I <sub>D</sub> = -250μA, V	<sub>DS</sub> = V <sub>GS</sub>
Static Drain-Source On-Resistance (Note 6)	P			0.125	Ω	$V_{GS}$ = -10V, $I_D$	= -2.3A
Static Drain-Source On-Resistance (Note 0)	R <sub>DS (ON)</sub>			0.190	12	$V_{GS} = -4.5V, I_{E}$	) = -1.9A
Forward Transconductance (Notes 6 & 7)	<b>g</b> fs	_	4.7	_	S	$V_{DS}$ = -15V, $I_D$	= -2.3A
Diode Forward Voltage (Note 6)	V <sub>SD</sub>	_	-0.85	-0.95	V	$I_{\rm S} = -2.0 \text{A}, V_{\rm GS} = 0 \text{V}$	
Reverse recovery time (Note 7)	t <sub>rr</sub>		25.1	_	ns		
Reverse recovery charge (Note 7)	Qrr	_	27.2	_	nC		
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C <sub>iss</sub>	_	637	—	pF	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V f = 1MHz	
Output Capacitance	C <sub>oss</sub>	_	70	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	53	_	pF	1 - 110112	
Total Gate Charge (Note 8)	Qg	_	9.0	—	nC	$V_{GS} = -4.5V$	
Total Gate Charge (Note 8)	Qg	_	17.7	_	nC		$V_{DS} = -30V$
Gate-Source Charge (Note 8)	Q <sub>gs</sub>	_	1.6	_	nC	$V_{GS} = -10V$	$I_{D} = -2.2A$
Gate-Drain Charge (Note 8)	Q <sub>gd</sub>		4.4	_	nC		
Turn-On Delay Time (Note 8)	t <sub>D(on)</sub>	_	2.6	_	ns		
Turn-On Rise Time (Note 8)	tr		3.4	_	ns	$V_{DD} = -30V, V_{GS} = -10V$	
Turn-Off Delay Time (Note 8)	t <sub>D(off)</sub>	_	26.2	_	ns	$I_D = -1A, R_G \cong 6.0\Omega$	
Turn-Off Fall Time (Note 8)	tf	_	11.3	_	ns	7	

Notes:

Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%
For design aid only, not subject to production testing.
Switching characteristics are independent of operating junction temperatures.



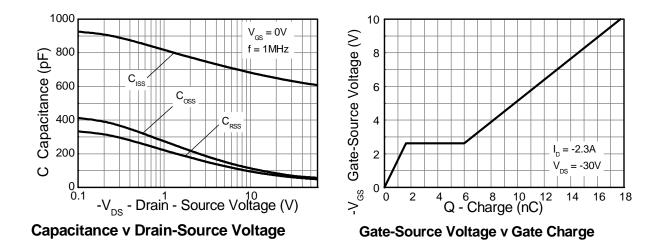
# **Typical Characteristics**



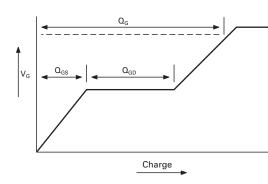




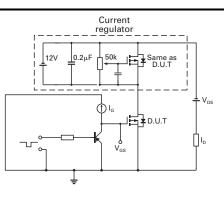
# **Typical Characteristics - continued**



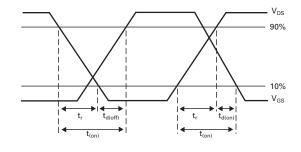
# **Test Circuits**



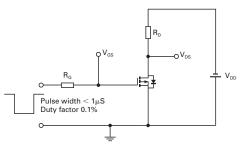




Gate charge test circuit



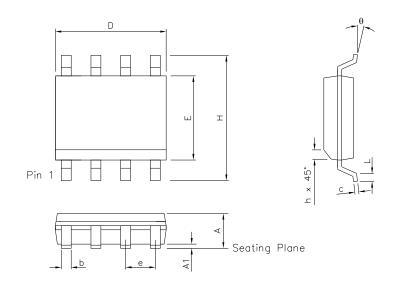
Switching time waveforms



#### Switching time test circuit

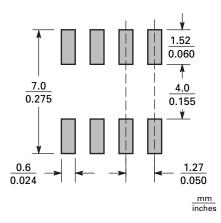


# **Package Outline Dimensions**



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
А	0.053	0.069	1.35	1.75	е	0.050 BSC		1.27 BSC	
A1	0.004	0.010	0.10	0.25	b	0.013	0.020	0.33	0.51
D	0.189	0.197	4.80	5.00	С	0.008	0.010	0.19	0.25
Н	0.228	0.244	5.80	6.20	θ	0°	8°	0°	8°
E	0.150	0.157	3.80	4.00	h	0.010	0.020	0.25	0.50
L	0.016	0.050	0.40	1.27	-	-	-	-	-

# Suggested Pad Layout





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